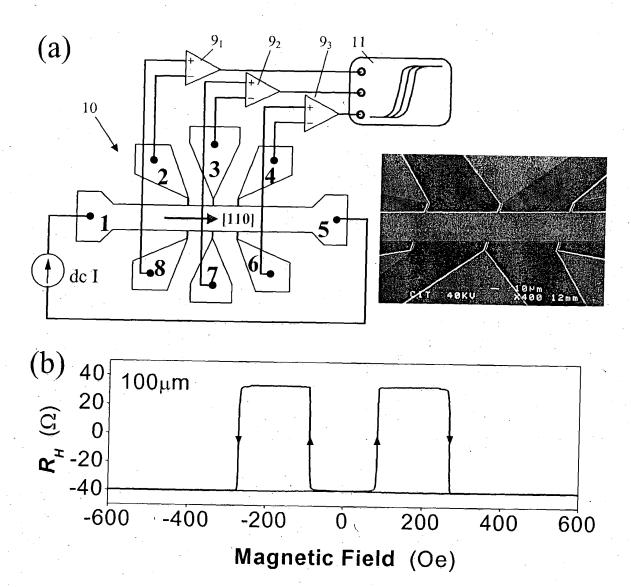
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**FIG.** 1.

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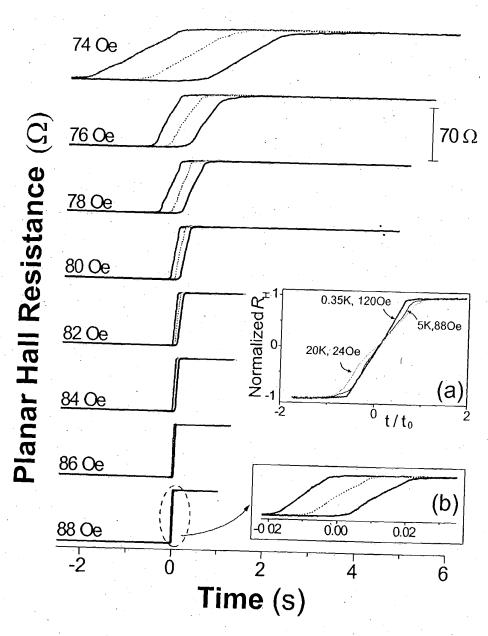
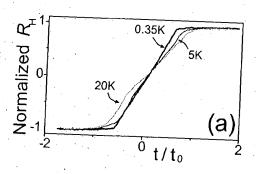


FIG. 2 (a) and (b)

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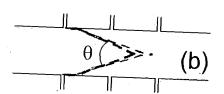


FIG. 2(c).

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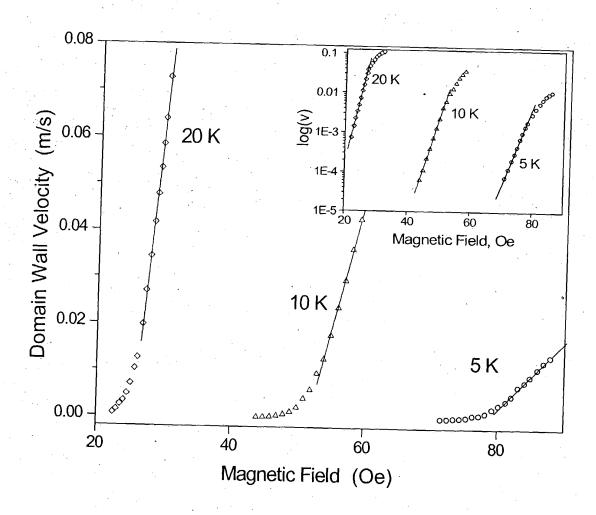


FIG. 3.

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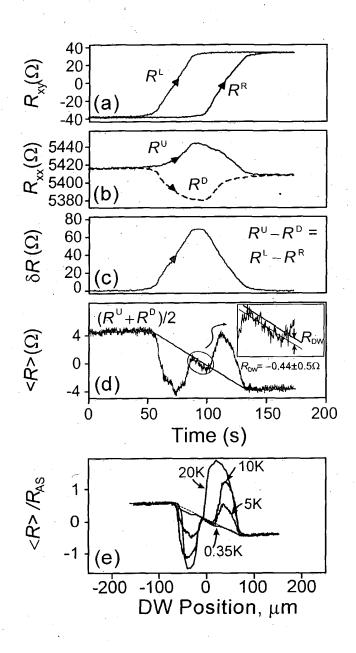
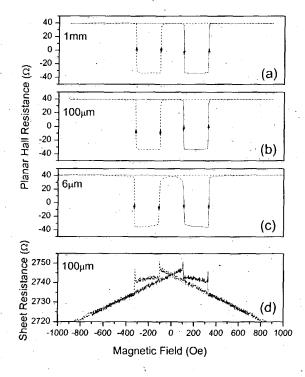
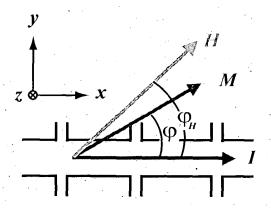


FIG. 4.

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FIG. 5





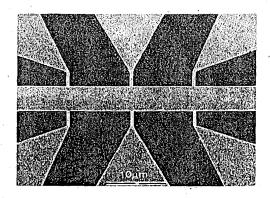


FIG. 5(e)

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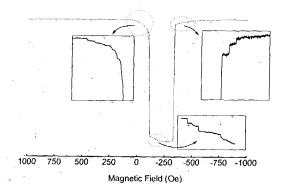


FIG. 5(f)

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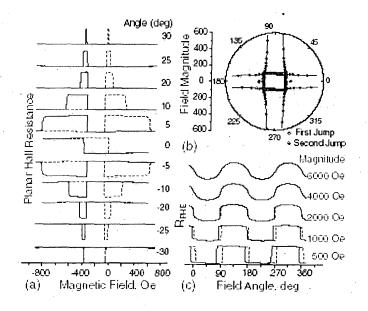


FIG. 6

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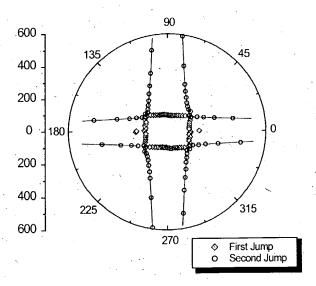


FIG. 6(b)

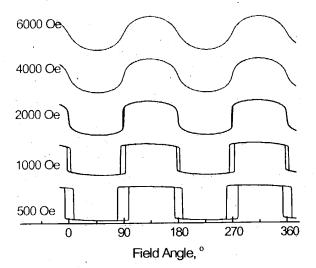


FIG. 6 (c)

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6000 (a) (b) 150-50.0K 4800  $\Delta R_{_{H}}(\Omega)$ 100 <sup>3600</sup> ය යි. 40.0K Planar Hall Resistance  $(\Omega)$ 50 30.0K 2400 0 20.0K log(T) 10.0K (c) 0.03 ×10<sup>-6</sup> <del>↑</del> ⊿R<sub>H</sub>/R<sub>□</sub> ♦— Squid M 10 4.77K 0.02 M (a.u.) 1.32K 6 0.01 50 0.32K O 2 -50 0.00 -1000 -500 Ö, 500 1000 20 10 30 40 Magnetic Field (Oe) Temperature (K)

**FIG.** 7

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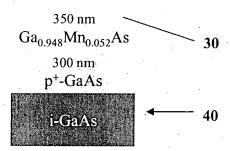
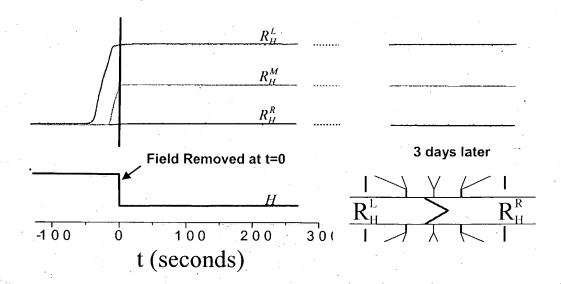


FIG. 9



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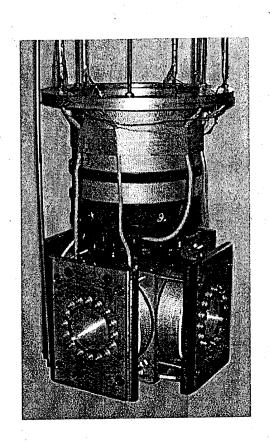


FIG. 10

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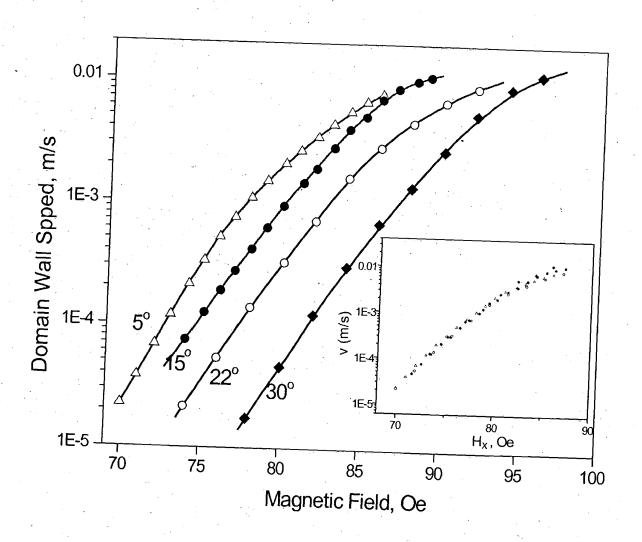


FIG. 11